

# 3 A High Voltage Schottky Barrier Rectifier

#### **DESCRIPTION**

This UPS3100e3 in the Powermite3® package is a high efficiency Schottky rectifier that is also RoHS compliant offering high current/power capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies. In addition to its size advantages, the Powermite3® package includes a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly and a unique locking tab act as an efficient heat path to the heat-sink mounting. Its innovative design makes this device ideal for use with automatic insertion equipment.

**IMPORTANT:** For the most current data, consult *MICROSEMI*'s website: http://www.microsemi.com

## KEY FEATURES

- Very low thermal resistance package
- RoHS Compliant with e3 suffix part number
- Guard-ring-die construction for transient protection
- Efficient heat path with Integral locking bottom metal tab
- Low forward voltage
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion
- Low profile-maximum height of 1mm

# ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

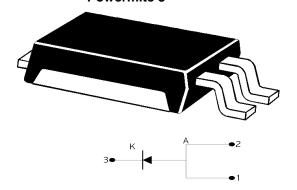
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} egin{array}{c} egin{array}{c} V_{RMM} \ V_{R} \end{array}$	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Rectified Output Current	Io	3	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T <sub>c</sub> =90 °C	I <sub>FSM</sub>	50	А
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C
Junction Temperature	$T_J$	-55 to +125	°C

#### THERMAL CHARACTERISTICS

Thermal Resistance			
Junction-to-Case (bottom)	$R_{\theta JC}$	2.5	°C/ Watt
Junction to Ambient (1)	Rain	65	°C/ Watt

(1) When mounted on FR-4 PC board using 2 oz copper with recommended minimum foot print

## Powermite 3™



#### APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Silicon Schottky (hot carrier) rectifier for minimal reverse voltage recovery
- Elimination of reverse-recovery oscillations to reduce need for EMI filtering
- Charge Pump Circuits
- Reduces reverse recovery loss with low I<sub>RM</sub>
- Small foot print 190 X 260 mils (1:1 Actual size)
   See mounting pad details on pg 3

#### **MECHANICAL & PACKAGING**

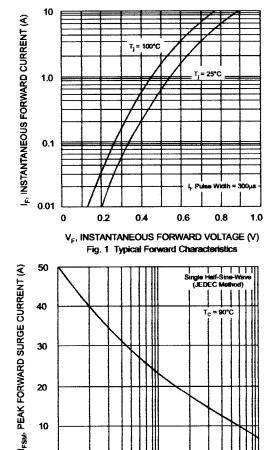
- CASE: Void-free transfer molded thermosetting epoxy compound meeting UL94V-0
- FINISH: Annealed matte-Tin plating over copper and readily solderable per MIL-STD-750 method 2026 (consult factory for Tin-Lead plating)
- POLARITY: See figure (left)
- MARKING: S3100•
- WEIGHT: 0.072 gram (approx.)
- · Package dimension on last page
- Tape & Reel option: 16 mm tape per Standard EIA-481-B, 5000 on 13" reel

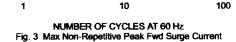


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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)						
Parameter	Symbol	Conditions	Min	Тур.	Max	Units
Forward Voltage (Note 1)	V <sub>F</sub>	$I_F = 3 \text{ A}$ , $T_j = 25 \text{ °C}$ $I_F = 3 \text{ A}$ , $T_j = 100 \text{ °C}$ $I_F = 6 \text{ A}$ , $T_j = 25 \text{ °C}$ $I_F = 6 \text{ A}$ , $T_i = 100 \text{ °C}$		0.72 0.60 0.79 0.68	0.76 0.64 0.83 0.72	V
Reverse Break Down Voltage (Note 1)	$V_{BR}$	I <sub>R</sub> = 0.2 mA	100			V
Reverse Current (Note1)	I <sub>F</sub>	V <sub>R</sub> = 100V, T <sub>j</sub> = 25 °C V <sub>R</sub> = 100V, T <sub>j</sub> =100 °C		1.5 0.5	200 20	μA mA
Capacitance	C <sub>T</sub>	V <sub>R</sub> = 4 V; f = 1 MHz		85		pF

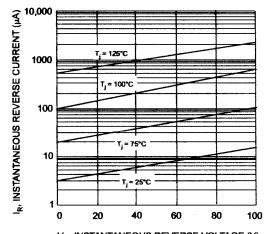
Note: 1 Short duration test pulse used to minimize self – heating effect.





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V<sub>R</sub>, INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 2 Typical Reverse Characteristics

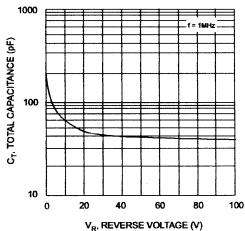
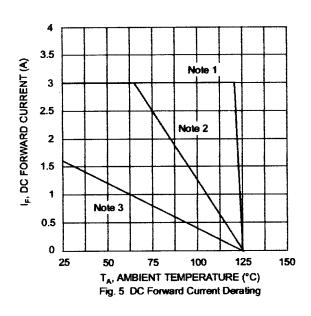


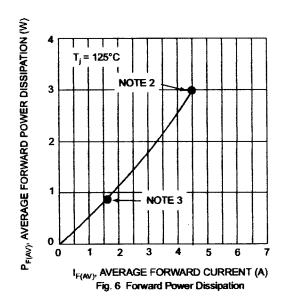
Fig. 4 Typical Capacitance vs. Reverse Voltage

100



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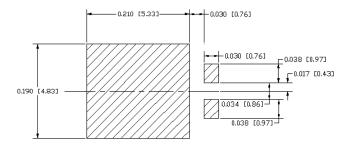




Notes: 1.  $T_A = T_{SOLDERING\ POINT}$ ,  $R_{\Theta JS} = 2.5 \text{C/W}$ ,  $R_{\Theta SA} = 0^{\circ} \text{C/W}$ .

- 2. Device mounted on GETEK substrate, 2" x 2", 2 oz. copper , double-sided , cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\Theta JA}$  in range of 20-35°C/W.
- 3. Device mounted on FRA-4 substrate, 2" x 2", 2 oz. copper, single-sided, pad layout  $R_{\Theta JA}$  in range of 65°C/W. See mounting pad below.

#### **MOUNTING PAD DIMENSIONS**

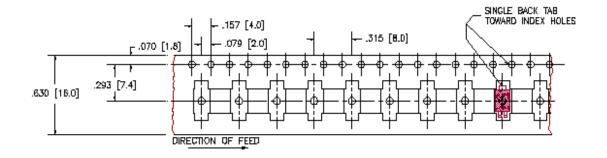


Mounting Pad Dimensions: inches [mm]

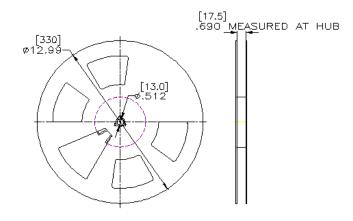


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#### **TAPE & REEL**



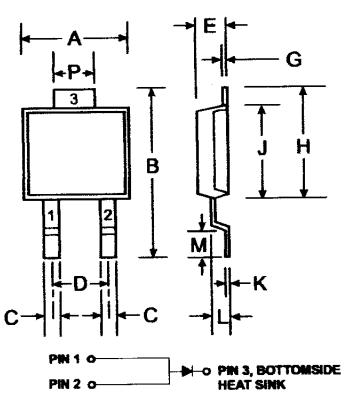
#### 13 INCH REEL





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## **PACKAGE DIMENSIONS**



POWERMITE®3			
Dim	Min Max		
A	4.03	4.09	
В	6.40	6.61	
С	.889 NOM		
D	1.83 NOM		
E	1.10	1.14	
G	.178 NOM		
Н	5.01	5.17	
J	4.37	4.43	
K	.178 NOM		
L	.71	.77	
M	.36	.46	
P	1.73	1.83	
All Dimensions in mm			

Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

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